



ALTERNATIVE TO PTO/SB/08a/b (06-03)

Substitute Form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	09/759,312
				Filing Date	January 12, 2001
				First Named Inventor	Yoshihiro UETA
				Art Unit	2812
				Examiner Name	S. Mulpuri
Sheet	1	of	1	Attorney Docket Number	299002051800

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	1.	Zauner, A.R.A. et al. (1999). "Homoeopitaxial Growth on Misoriented GaN Substrates By MOCVD," <i>Proceedings of the Material Research Society Symposium W (GaN and Related Alloys) November 28-December 3, 1999</i> , 595:407 (Abstract W6.3).	

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Examiner Signature		Date Considered	2/2/03
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